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PATENT

5 forming a gate on the gate oxide;  
6 implanting a first pocket implant into the semiconductor substrate from a  
7 first side of the gate; and  
8 implanting a second pocket implant into the semiconductor substrate from  
9 a second side of the gate, wherein the first pocket implant is near and separated by a  
10 small distance from the second pocket implant.

*SUG37*

*CH*

1 38. (Amended) A method of fabricating a transistor in an integrated  
2 circuit device comprising:  
3 providing a semiconductor substrate having a surface;  
4 forming a gate oxide on the semiconductor substrate surface;  
5 forming a gate on the gate oxide;  
6 implanting a first pocket implant into the semiconductor substrate from a  
7 first side of the gate at an angle; and  
8 implanting a second pocket implant into the semiconductor substrate from  
9 a second side of the gate at an angle,  
10 wherein a concentration of the pocket implants under the gate is  
11 nonuniform, and the pocket implants extend near the semiconductor substrate surface.

*CH*

1 41. (New) The method of claim 27 wherein the first pocket  
2 implant is separated from the second pocket implant by approximately 0.35 microns.